

CLAIMS

What is claimed is:

1. A method of producing variable rate filtered samples for use as data in a
5 secondary process that has prescribed time intervals during which filtered samples are
required, comprising:
producing multiple respective periodic sequences of filtered samples each
having a same sample period, wherein each respective sequence can provide a
different filtered sample during each sample period and the respective sequences are
10 offset in time with respect to one another so that no filtered sample from any
sequence overlaps with any filtered sample from any other sequence; and
selecting from among the respective sequences filtered samples that coincide
with the timing requirements of the secondary process.
- 15 2. The method of claim 1, wherein selecting is done from at least one of the
respective sequences.
3. The method of claim 1, wherein selecting is done from at least two of the
respective sequences.
- 20 4. The method of claim 1, wherein selecting is done from at least three of the
respective sequences.
5. The method of claim 1, wherein selecting is done from at least four of the
25 respective sequences.
6. The method of claim 1, wherein selecting is performed sequentially and
periodically from at least two of the respective sequences.

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7. The method of claim 1, wherein:
each respective sequence has a same filter sampling time;
selecting is performed every prescribed time interval; and
5 the same filter sampling time is less than the prescribed time interval.
8. The method of claim 1, further comprising generating, from a sensor, sensor
samples that are used to produce the filtered samples.
- 10 9. The method of claim 8, further comprising controlling a lithographic system
using the filtered samples, wherein the sensor samples are indicative of a position of a
stage assembly.
10. The method of claim 9, wherein the stage assembly positions at least one
15 reticle.
11. The method of claim 9, wherein the stage assembly positions at least one
wafer.
- 20 12. The method of claim 9, wherein producing generates an output sequence
comprising a sample train of output samples as filtered samples.
13. The method of claim 1, wherein the sequences have a quantity equal to a value
governed by the expression: value = maximum of $\{(T_f/T_{be}) * n$, for all allowable $T_{be}\}$,
25 where n is a smallest integer that will result in an integer value for $(T_f/T_{be}) * n$, T_f is a
filter sampling time and T_{be} is a prescribed time interval.

14. The method of claim 13, wherein selecting is performed every prescribed time interval, further comprising changing the prescribed time interval T_{be} .

15. The method of claim 1, wherein selecting is performed every prescribed time interval, further comprising changing the prescribed time interval T_{be} , wherein the prescribed time interval T_{be} comprises a blanking time T_b and an exposure time T_e and changing the prescribed time interval T_{be} comprises increasing the exposure time T_e .

16. The method of claim 1, wherein selecting is performed every prescribed time interval, further comprising:

changing the prescribed time interval T_{be} , wherein the prescribed time interval T_{be} comprises a blanking time T_b and an exposure time T_e and each respective sequence has a respective filter sampling time T_f ; and

changing the respective filter sampling time T_f of each of the respective sequences.

17. The method of claim 16, wherein changing the respective filter sampling time T_f comprises decreasing the respective filter sampling time T_f .

18. The method of claim 16, wherein changing the prescribed time interval T_{be} comprises increasing the prescribed time interval T_b .

19. The method of claim 1, wherein the secondary process has multiple input sample windows during which it accepts samples, further comprising selecting from among the respective sequences filtered samples that result in respective coincidences of the selected filtered samples and the respective input sample windows for the secondary process.

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periodically accept the filtered output;

accepting a sensor sample by the synchronous filter;

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accepting the filtered output by the secondary process.

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lithography source.

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sensor sample.

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reticle.

26. The method of claim 24, wherein the stage assembly positions at least one wafer.

5 27. The method of claim 22, wherein:
the lithography source generates a beam of charged particles;
the beam has a deflection; and
controlling the lithography source comprises adjusting the deflection of the
beam.

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28. The method of claim 20, further comprising increasing the secondary process period T_{be} such that the synchronous filter generates the filtered output when the secondary process is able to periodically accept the filtered output.

15 29. The method of claim 28, wherein the secondary process period T_{be} comprises a blanking time T_b and an exposure time T_e and increasing the secondary process period T_{be} comprises increasing the blanking time T_b .

20 30. The method of claim 20, further comprising increasing the secondary process period T_{be} wherein:

the secondary process period T_{be} comprises a blanking time T_b and an exposure time T_e ;

increasing the secondary process period T_{be} comprises increasing the blanking time T_b ; and

25 after increasing the blanking time T_b , the secondary process period T_{be} is substantially an integer multiple of the filter sampling time T_f .

5 increasing the secondary process period T_{be} by an amount such that the
secondary process is able to periodically accept the filtered output at substantially the
same time the synchronous filter produces the filtered output;
 accepting a sensor sample by the synchronous filter;
 generating the filtered output from the synchronous filter using the sensor
10 sample; and
 accepting the filtered output by the secondary process.

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37. The method of claim 35, wherein the stage assembly positions at least one wafer.

38. The method of claim 33, wherein:
the lithography source generates a beam of charged particles;
the beam has a deflection; and
5 controlling the lithography source comprises adjusting the deflection of the
beam.

39. The method of claim 31, further comprising increasing the secondary process
period T_{be} such that the synchronous filter also generates the filtered output when the
10 secondary process is able to periodically accept the filtered output, wherein:
the secondary process period T_{be} comprises a blanking time T_b and an
exposure time T_e ; and
increasing the secondary process period T_{be} comprises increasing the blanking
time T_b .

15 40. The method of claim 31, further comprising increasing the secondary process
period T_{be} , wherein:
the secondary process period T_{be} comprises a blanking time T_b and an
exposure time T_e ;
20 increasing the secondary process period T_{be} comprises increasing the blanking
time T_b ; and
after increasing the blanking time T_b , the secondary process period T_{be} is
substantially an integer multiple of the filter sampling time T_f .

25 41. A system for use with a secondary process that requires different filtered
samples during each of a sequence of input window time intervals, and for providing
filtered electronic signal samples, comprising:
multiple filtered sample lines;

multiple filters, each periodically receiving a sample of a signal; wherein:

each filter periodically provides its filtered sample sequence to a filtered sample line with a respective filter sampling time T_f , and

the respective filtered sample sequences are offset in time with respect to one another so that no filtered sample from any filtered sample sequence overlaps with any filtered sample from any other filtered sample sequence;

a multiplexer responsive to control signals and coupled to each of the multiple filtered sample lines; wherein:

the multiplexer accepts the respective periodic filtered output of each of the multiple filters, and

the multiplexer has a multiplexer output; and

control logic providing control signals causing the multiplexer to:

select from among the filtered sample lines in a sequence results in respective coincidences of respective filtered samples on respective selected filtered sample lines and respective input sample windows for the secondary process, and sequentially provide respective filtered samples on respective selected lines as a sequence of filtered input for use by the secondary process.

42. The system of claim 41, wherein the sequence of filtered input is produced using less than all of the respective filtered sample sequences accepted by the multiplexer.

43. The system of claim 41, wherein the secondary process is controlled using the sequence of filtered input.

44. The system of claim 41, wherein the secondary process comprises a source for lithography that is controlled using the sequence of filtered input.

45. The system of claim 41, further comprising a sensor that generates the signal.

46. The system of claim 45, further comprising an analog-to-digital converter that periodically generates the sample of the signal.

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47. The system of claim 46, wherein the sample is indicative of a position of a stage assembly.

48. The system of claim 47, wherein the stage assembly positions at least one
10 reticle.

49. The system of claim 47, wherein the stage assembly positions at least one wafer.

15 50. The system of claim 44, wherein:
the lithography source generates a beam of charged particles;
the beam has a deflection; and
the deflection of the beam is controlled by the sequence of filtered input.

20 51. The system of claim 41, wherein:
the secondary process has a prescribed time interval T_{be} by which the input sample windows are spaced; and
the prescribed time interval T_{be} is less than the filter sampling time T_f .

25 52. The system of claim 41, wherein:
the multiple filters are programmable filters; and
the respective filter sampling time of each programmable filter can be changed.

58. The system of claim 57, wherein the stage assembly positions at least one reticle.

5 59. The system of claim 57, wherein the stage assembly positions at least one wafer.

60. The system of claim 57, wherein the beam has deflection that is controlled by the output sequence.

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61. The system of claim 54, wherein a prescribed time interval T_{be} is less than the filter sampling time T_f .

62. The system of claim 54, wherein:

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the multiple synchronous filters have a quantity;

the sequence is a periodic sequence with a prescribed time interval T_{be} having multiple allowable values; and

the quantity is equal to a value governed by an expression: value = maximum of $\{(T_f/T_{be}) * n$, for all allowable $T_{be}\}$, where n is a smallest integer that will result in
20 an integer value for $(T_f/T_{be}) * n$.

63. A method of exposing a wafer to an electron beam in a microlithography apparatus, comprising:

25 acquiring, from a sensor, data indicative of a position of a stage assembly that positions the wafer;

calculating, from the data, a velocity of the stage assembly and an acceleration of the stage assembly;

estimating, using the velocity and the acceleration, a future position of the stage assembly;

determining a difference between the position and the future position; and
adjusting at least one of:

- 5 the position within a predetermined position error, and
 a deflection amount of the electron beam.

64. The method of claim 63, wherein acquiring comprises asynchronous data acquisition.

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